Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low leakage current
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic

3. Applications

- · High frequency switched-mode power supplies
- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 109 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	10	А
Static charact	eristics						
V _F	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>		-	-	1.6	٧
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	20	-	ns





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYV10-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Marking

Table 4. Marking codes

Type number	Marking code
BYV10-600P	BYV10-600P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 109 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _{mb} ≤ 109 °C; square-wave pulse	-	20	А

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Symbol	Parameter	Conditions	Min	Max	Unit
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	80	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	88	Α
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

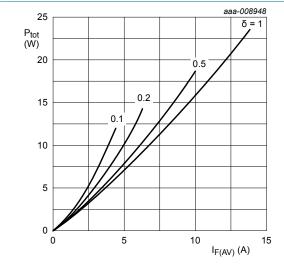


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 1.268 \text{ V}; \text{ R}_{S} = 0.031 \Omega \end{split}$$

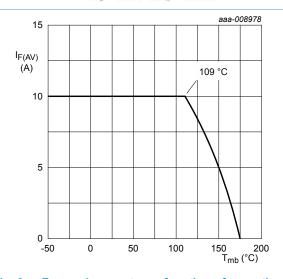


Fig. 3. Forward current as a function of mounting base temperature; maximum values

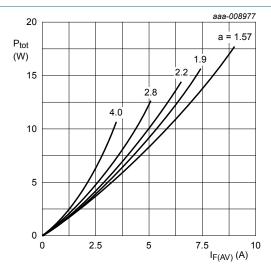


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

 $V_O = 1.268 \text{ V}; R_S = 0.031 \Omega$

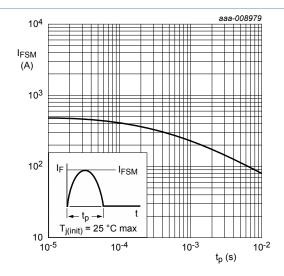


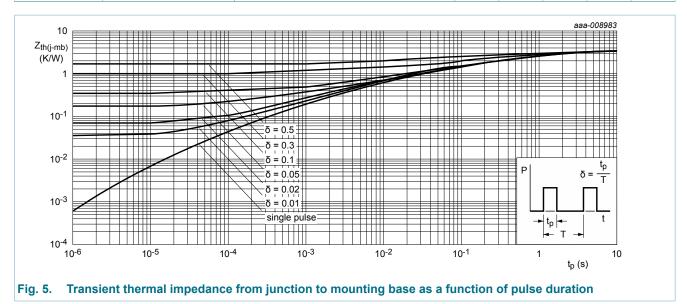
Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	3.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static characteristics							
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.5	2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>		-	-	1.6	V
I _R reverse current	reverse current	V _R = 600 V; T _j = 25 °C		-	-	10	μA
		V _R = 500 V; T _j = 150 °C		-	-	250	μA
Dynamic cl	haracteristics	1	I				
t _{rr} reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	35	50	ns	
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	20	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_F = 10 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A}$ /	-	40	-	ns
		μs; T _j = 25 °C; <u>Fig. 7</u>				

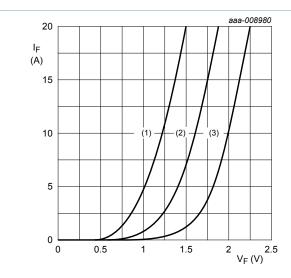


Fig. 6. Forward current as a function of forward voltage

(1) $T_j = 150$ °C; typical values; (2) $T_j = 150$ °C; maximum values; (3) $T_j = 25$ °C; maximum values; $V_Q = 1.268$ V; $R_S = 0.031$ Ω

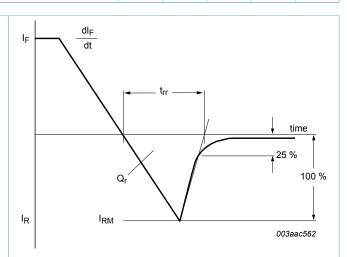
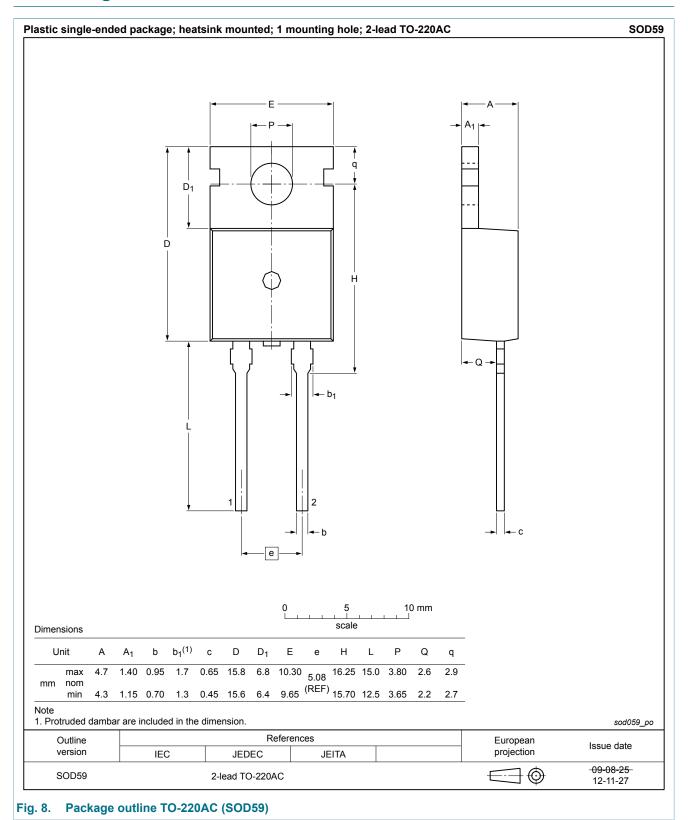


Fig. 7. Reverse recovery definitions; ramp recovery

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11. Package outline



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12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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